

REMARKS/ARGUMENTS

Claims 58-62 stand in the present application, claims 59-62 having been added. Reconsideration and favorable action is respectfully requested in view of the above amendments and the following remarks.

In the Office Action, the Examiner has first noted that the Information Disclosure Statement filed on July 1, 2003 failed to comply with 37 CFR 1.98(a)(2), which requires copies of each U.S. and foreign patent. As suggested by the Examiner, Applicants have resubmitted available duplicate copies of the foreign references which were listed on the PTO-1449 form which accompanied the IDS filed on July 1, 2003. However, Applicants are in the process of obtaining additional duplicate copies of others of the listed references, and will submit those as soon as those duplicate copies are obtained.

The Examiner has also objected to the specification for not containing the updated patent issued numbers of the aforementioned parent applications. As noted above, Applicants have amended the specification in order to correct this deficiency.

The Examiner has also rejected claim 58 under 35 U.S.C. § 102(e) as being anticipated by Manabe et al. Applicants respectfully traverse the rejection.

Claim 58 explicitly recites a light-transmitting first electrode and a second electrode for bonding. The light-transmitting first electrode is provided over a surface of the p-type semiconductor layer. Thus, the emitted light can be conducted from the bonding side of the device. In addition, the second electrode is adhered to the p-type gallium nitride based compound semiconductor layer stronger than a bond of the p-type gallium nitride based compound semiconductor layer with the first electrode or than a bond of the first electrode with the second electrode. With this recited structure, peeling

off of the electrode during bonding can be effectively prevented. Further, since the second electrode is provided for bonding, the second electrode is formed on a small area on the first electrode. In other words, the second electrode constitutes a bonding pad. This is clearly defined in new claim 62.

Manabe et al. disclose a light-emitting diode having an electrode 7 of aluminum on a p-type impurity doped GaN layer 5. The aluminum electrode 7 is formed on an underlying nickel layer 13 and covers the nickel layer 13 entirely. The aluminum electrode 7 does not constitute a bonding pad. Further, Manabe et al. do not disclose or suggest that the nickel layer 13 or the aluminum electrode 7 is light-transmitting. In addition, Manabe et al. do not disclose or suggest that the GaN layer 5 is of a p-type. The "p-type impurity doped GaN layer" disclosed and claimed in Manabe et al. does not uniquely mean that it is of p-type. Rather, Manabe et al. merely indicates that the GaN layer 5 is doped with a p-type impurity.

In view of the above, Applicants respectfully submit that the present invention is not taught or suggested by Manabe et al. Accordingly, claim 58 and its dependent claims 59-62 are believed to patentably define over the cited reference.

Therefore, in view of the above amendments and remarks, it is respectfully requested that the application be reconsidered and that all of claims 58-62, now standing in the application, be allowed and that the case be passed to issue. If there are any other issues remaining which the Examiner believes could be resolved through either a supplemental response or an Examiner's amendment, the

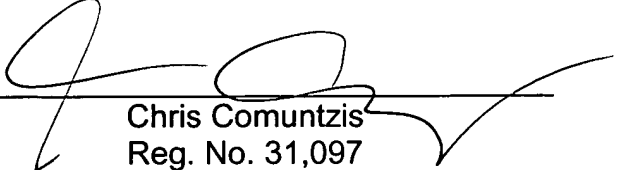
NAKAMURA et al.
Appl. No. 10/609,410
July 29, 2004

Examiner is respectfully requested to contact the undersigned at the local
telephone exchange indicated below.

Respectfully submitted,

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